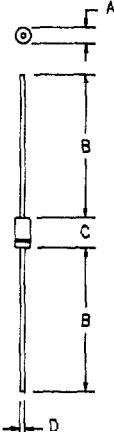


1 Amp Schottky Rectifier

1N5817G, 1N5818G, 1N5819G



Dim. Inches		Millimeter				
		Minimum	Maximum	Minimum	Maximum	Notes
A	.081	.107	2.057	2.718		Dia.
B	1.10	—	27.94	—		
C	.160	.205	4.064	5.207		
D	.028	.034	.711	.864		Dia.

GLASS HERMETIC D041G

Microsemi
Catalog Number

Working
Peak Reverse
Voltage

Repetitive
Peak Reverse
Voltage

1N5817G
1N5818G
1N5819G

20V
30V
40V

20V
30V
40V

- Schottky Barrier Rectifier
- Guard Ring Protection
- Low Forward Voltage
- High Reliability
- High Current Capability

Electrical Characteristics

		5817G	5818G	5819G	
Average forward current	I F(AV)	1A	1A	1A	
Ambient Temperature		135°C	130°C	130°C	R _{θJL} = 35°C/W, L = 0"
Ambient Temperature		125°C	117°C	117°C	R _{θJL} = 60°C/W, L = 3/8"
Maximum surge current	I FSM	50A	50A	50A	8.3ms, half sine, T _J = 150°C
Max peak forward voltage	V FM	.36V	.39V	.39V	I FM = 0.1A; T _J = 25°C *
Max peak forward voltage	V FM	.45V	.55V	.55V	I FM = 1.0A; T _J = 25°C *
Max peak forward voltage	V FM	.65V	.85V	.85V	I FM = 3.0A; T _J = 25°C *
Max peak reverse current	I RM	1mA	1mA	1mA	V _{RRM} , T _J = 25°C
Typical junction capacitance	C J	105pF	50pF	50pF	V _R = 5.0V, T _J = 25°C

*Pulse test: Pulse width 300 μ sec, Duty cycle 2%

Thermal and Mechanical Characteristics

Storage temperature range
Operating junction temp range

T_{STC}

-65°C to 150°C

Maximum thermal resistance

T_J
L = 3/8" R_{θJL}
L = 0 R_{θJL}

-65°C to 150°C

60°C/W

Junction to Lead

35°C/W

Junction to Lead

Weight

.012 ounces (0.38 grams) typical

1N5817G

C

Figure 1
Typical Forward Characteristics

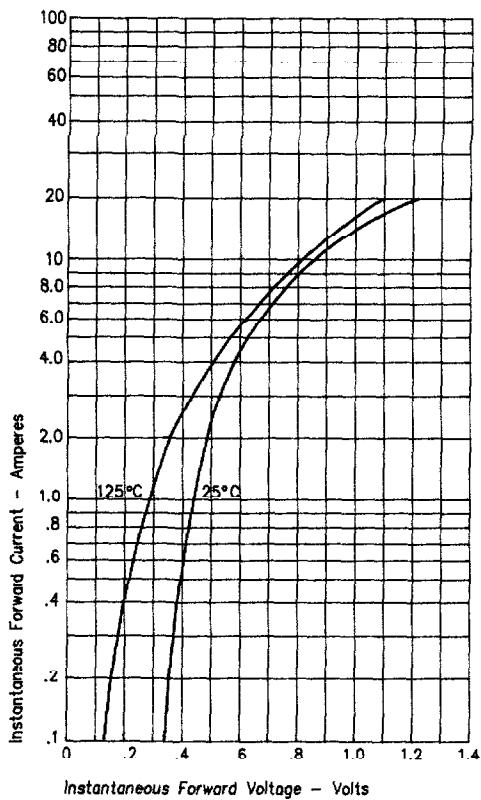


Figure 3
Typical Junction Capacitance

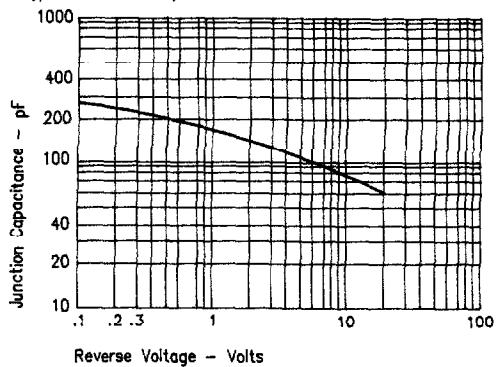
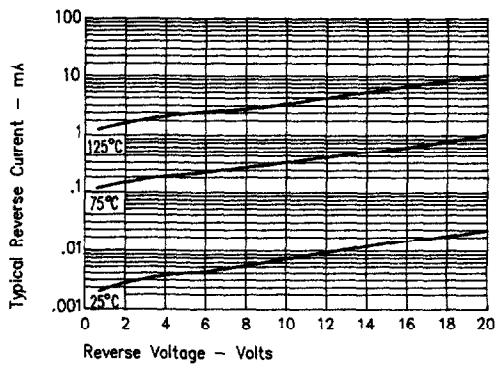


Figure 2
Typical Reverse Characteristics



1N5818G & 1N5819G

Figure 1
Typical Forward Characteristics

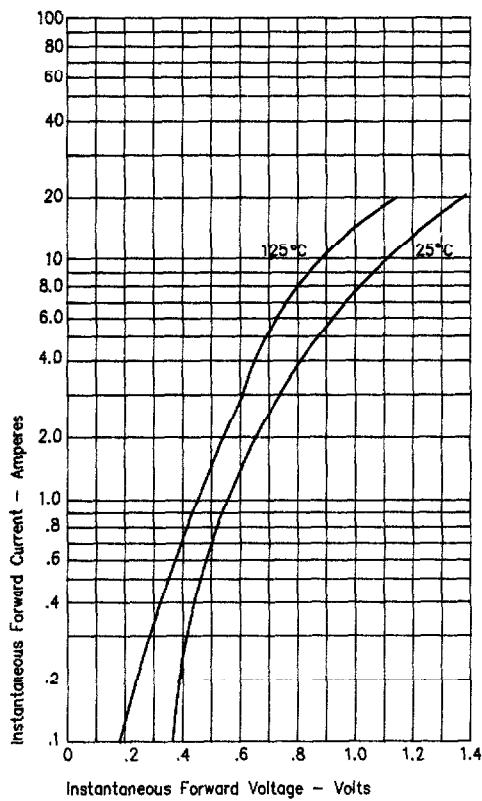


Figure 3
Typical Junction Capacitance

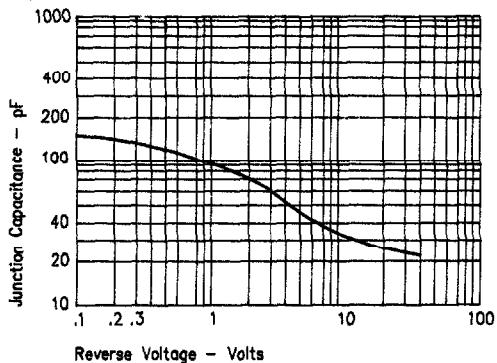


Figure 2
Typical Reverse Characteristics

